



PSMN2R9-100SSE

N-channel 100 V, 2.9 mOhm MOSFET with enhanced SOA in LFPAK88

20 June 2022

Preliminary data sheet

1. General description

N-channel enhancement mode MOSFET in a LFPAK88 package qualified to 175 °C. Part of Nexperia's "ASFETs for hotswap" portfolio, the PSMN2R9-100SSE delivers very low R_{DSon} and a very strong linear-mode (SOA) performance in a high-reliability copper-clip LFPAK88 package.

PSMN2R9-100SSE complements the latest "hot-swap" controllers - robust enough to withstand substantial inrush currents during turn-on, low R_{DSon} to minimize I^2R losses and deliver optimum efficiency when turned fully ON.

2. Features and benefits

- Fully optimized Safe Operating Area (SOA) for superior linear mode operation
- Low R_{DSon} for low I^2R conduction losses
- LFPAK88 package for applications that demand the highest performance and reliability

3. Applications

- Hot swap
- Load switch
- Soft start
- E-fuse
- Telecommunication systems based on a 48 V backplane/supply rail

4. Quick reference data

Table 1. Quick reference data

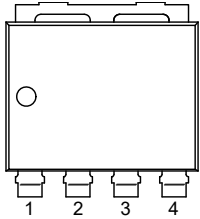
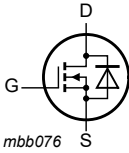
| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|--|--|-----|------|-----|------|
| V_{DS} | drain-source voltage | $25\text{ °C} \leq T_j \leq 175\text{ °C}$ | - | - | 100 | V |
| I_D | drain current | $V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; Fig. 2 | - | - | 210 | A |
| P_{tot} | total power dissipation | $T_{mb} = 25\text{ °C}$; Fig. 1 | - | - | 341 | W |
| T_j | junction temperature | | -55 | - | 175 | °C |
| Static characteristics | | | | | | |
| R_{DSon} | drain-source on-state resistance | $V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $T_j = 25\text{ °C}$; Fig. 12 | - | 2.3 | 2.9 | mΩ |
| | | $V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $T_j = 100\text{ °C}$; Fig. 13 | - | 3.4 | 4.6 | mΩ |
| Dynamic characteristics | | | | | | |
| Q_{GD} | gate-drain charge | $I_D = 25\text{ A}$; $V_{DS} = 50\text{ V}$; $V_{GS} = 10\text{ V}$; $T_j = 25\text{ °C}$; Fig. 14 ; Fig. 15 | 6.4 | 21.3 | 49 | nC |
| $Q_{G(tot)}$ | total gate charge | | 63 | 125 | 188 | nC |
| Avalanche ruggedness | | | | | | |
| $E_{DS(AL)S}$ | non-repetitive drain-source avalanche energy | $I_D = 71\text{ A}$; $V_{sup} \leq 100\text{ V}$; $R_{GS} = 50\text{ Ω}$; $V_{GS} = 10\text{ V}$; $T_{j(init)} = 25\text{ °C}$; unclamped; $t_p = 124\text{ μs}$; Fig. 4 | [1] | - | 575 | mJ |

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---------------------------|------------------|---|-----|-----|-----|------|
| Source-drain diode | | | | | | |
| Q_r | recovered charge | $I_S = 25\text{ A}$; $di_S/dt = -100\text{ A}/\mu\text{s}$; $V_{GS} = 0\text{ V}$; $V_{DS} = 50\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 18 | - | 57 | - | nC |

[1] Protected by 100% test

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|---|---|
| 1 | G | gate |  <p>LFLPAK88 (SOT1235)</p> |  <p>mbb076</p> |
| 2 | S | source | | |
| 3 | S | source | | |
| 4 | S | source | | |
| mb | D | mounting base; connected to drain | | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|----------------|----------|--|---------|
| | Name | Description | Version |
| PSMN2R9-100SSE | LFLPAK88 | plastic, single-ended surface-mounted package (LFLPAK88); 4 leads; 2 mm pitch; 8 mm x 8 mm x 1.6 mm body | SOT1235 |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|----------------|--------------|
| PSMN2R9-100SSE | X2E9S10S |

8. Limiting values

Table 5. Limiting values

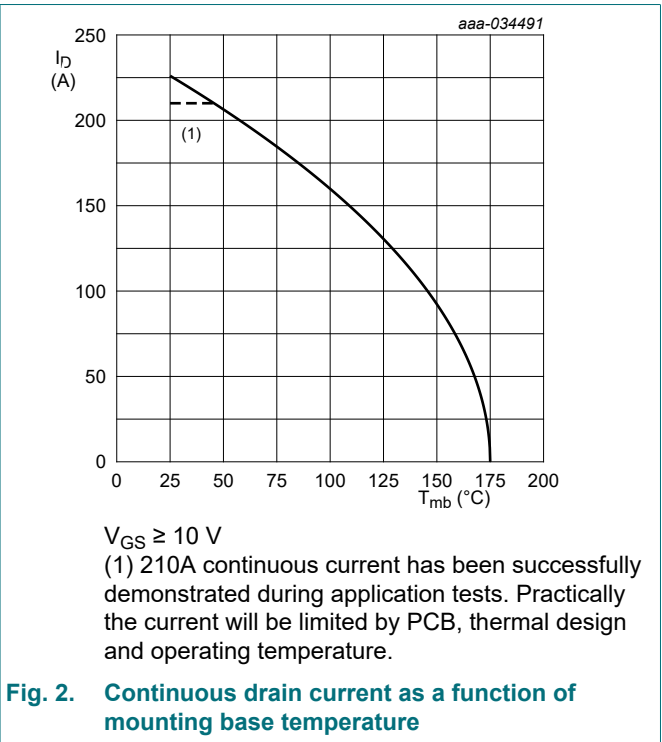
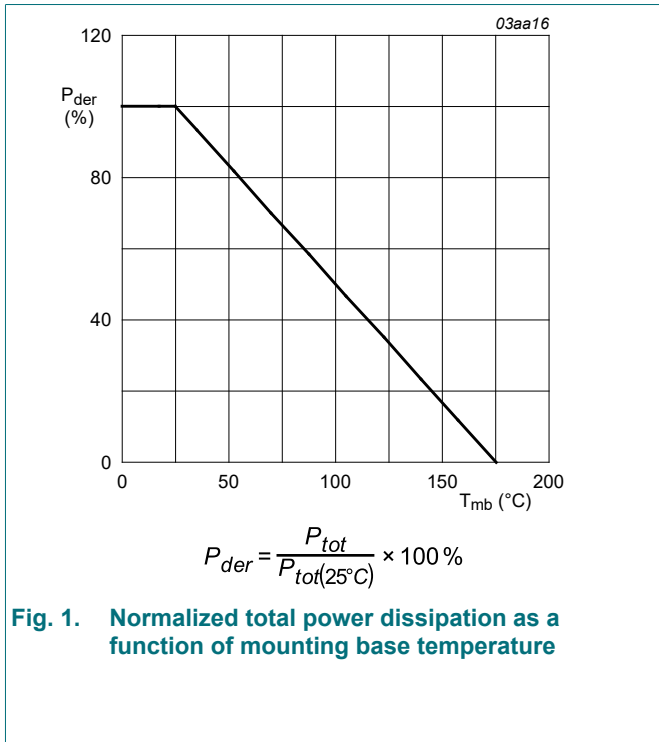
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-----------|-------------------------|---|-----|-----|------------------|
| V_{DS} | drain-source voltage | $25\text{ }^\circ\text{C} \leq T_j \leq 175\text{ }^\circ\text{C}$ | - | 100 | V |
| V_{DGR} | drain-gate voltage | $25\text{ }^\circ\text{C} \leq T_j \leq 175\text{ }^\circ\text{C}$; $R_{GS} = 20\text{ k}\Omega$ | - | 100 | V |
| V_{GS} | gate-source voltage | | -20 | 20 | V |
| P_{tot} | total power dissipation | $T_{mb} = 25\text{ }^\circ\text{C}$; Fig. 1 | - | 341 | W |
| I_D | drain current | $V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ }^\circ\text{C}$; Fig. 2 | - | 210 | A |
| | | $V_{GS} = 10\text{ V}$; $T_{mb} = 100\text{ }^\circ\text{C}$; Fig. 2 | - | 160 | A |
| I_{DM} | peak drain current | pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ }^\circ\text{C}$; Fig. 3 | - | 904 | A |
| T_{stg} | storage temperature | | -55 | 175 | $^\circ\text{C}$ |

N-channel 100 V, 2.9 mOhm MOSFET with enhanced SOA in LFPAK88

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-----------------------------|--|--|-----|-----|--------|
| T_j | junction temperature | | -55 | 175 | °C |
| $T_{sld(M)}$ | peak soldering temperature | | - | 260 | °C |
| Source-drain diode | | | | | |
| I_S | source current | $T_{mb} = 25\text{ °C}$ | - | 210 | A |
| I_{SM} | peak source current | pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$ | - | 904 | A |
| Avalanche ruggedness | | | | | |
| $E_{DS(AL)S}$ | non-repetitive drain-source avalanche energy | $I_D = 71\text{ A}$; $V_{sup} \leq 100\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $V_{GS} = 10\text{ V}$; $T_{j(init)} = 25\text{ °C}$; unclamped; $t_p = 124\text{ }\mu\text{s}$; Fig. 4 | [1] | - | 575 mJ |
| I_{AS} | non-repetitive avalanche current | $V_{sup} = 100\text{ V}$; $V_{GS} = 10\text{ V}$; $T_{j(init)} = 25\text{ °C}$; $R_{GS} = 50\text{ }\Omega$; Fig. 4 | [1] | - | 71 A |

[1] Protected by 100% test



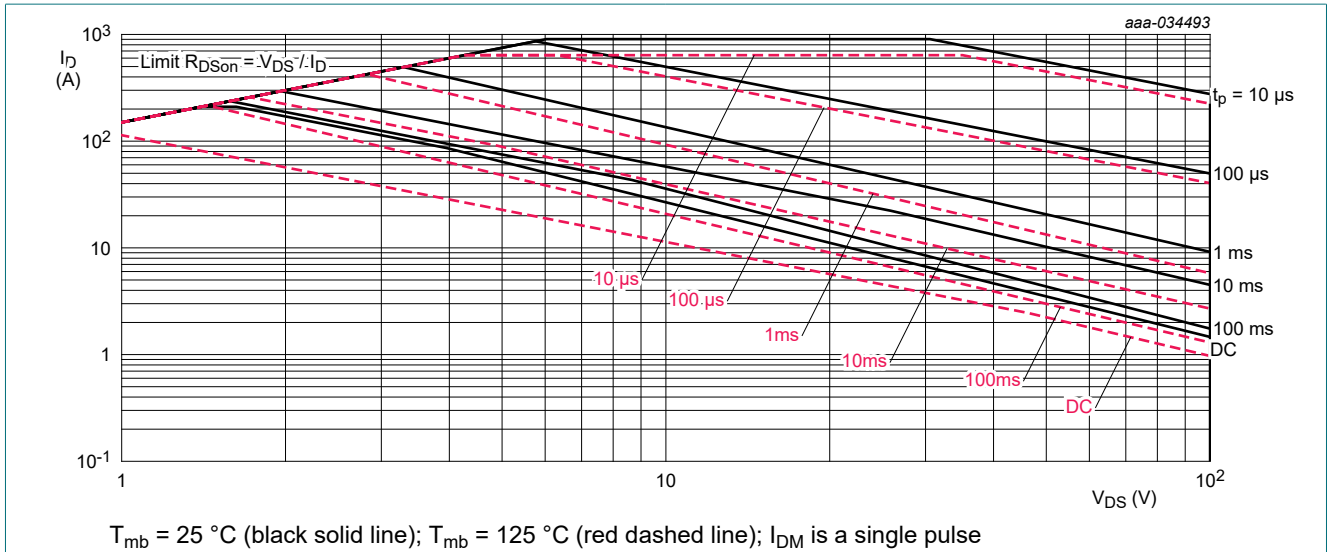


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

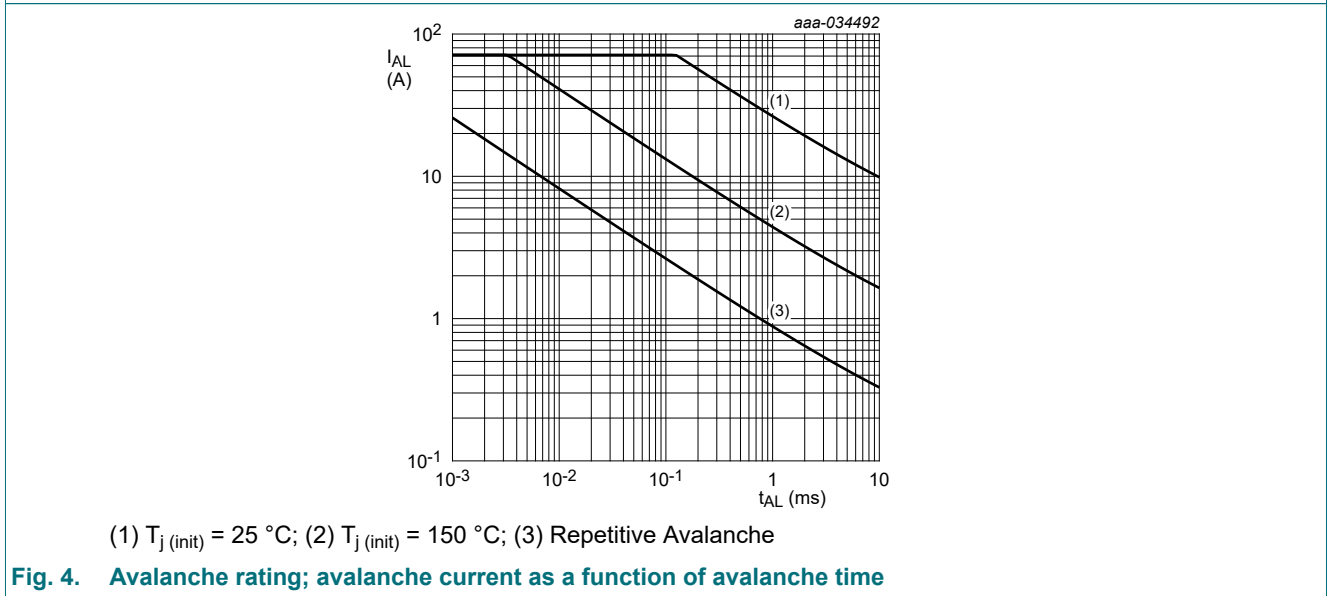


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|----------------|---|------------|-----|------|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Fig. 5 | - | 0.24 | 0.44 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | Fig. 6 | - | 35 | - | K/W |
| | | Fig. 7 | - | 70 | - | K/W |

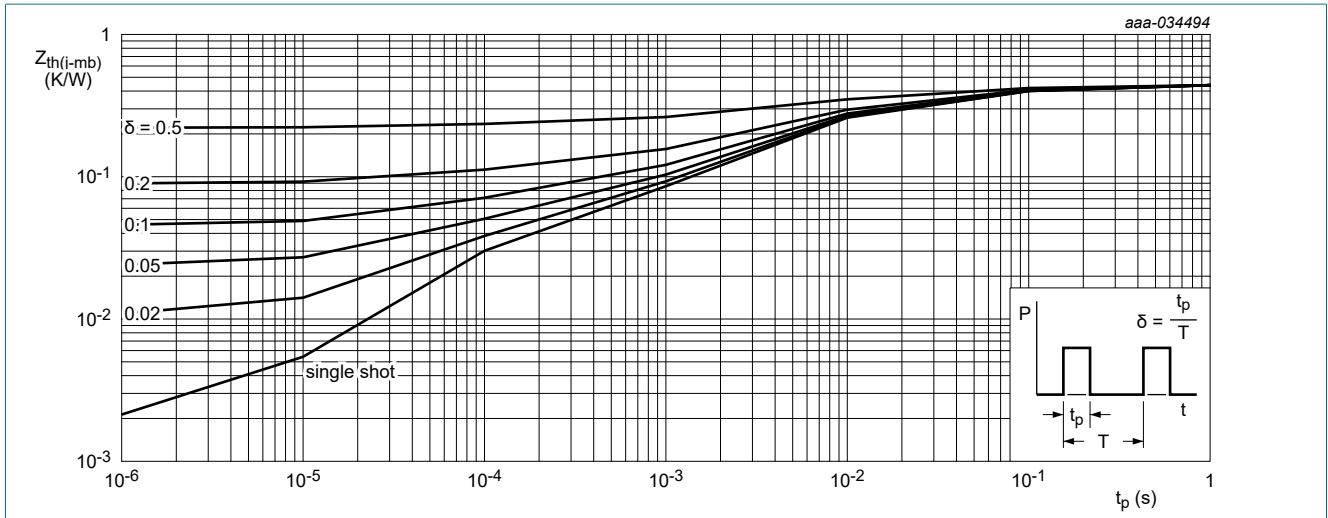


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

aaa-029383

Copper square 25.4 mm square; 70 μm thick on FR4 board

aaa-029384

70 μm thick copper on FR4 board

Fig. 6. PCB layout for thermal resistance from junction to ambient

Fig. 7. PCB layout with minimum footprint for thermal resistance from junction to ambient

10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-------------------------------|--|---|-----|------|-----|------|
| Static characteristics | | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$ | 100 | - | - | V |
| | | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$ | 90 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | $I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ }^\circ C; \text{ Fig. 11}$ | 2 | 3 | 3.6 | V |
| | | $I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 175 \text{ }^\circ C$ | - | 1.56 | - | V |
| | | $I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = -55 \text{ }^\circ C$ | - | 3 | - | V |
| $\Delta V_{GS(th)}/\Delta T$ | gate-source threshold voltage variation with temperature | $25 \text{ }^\circ C \leq T_j \leq 150 \text{ }^\circ C$ | - | -6.6 | - | mV/K |
| I_{DSS} | drain leakage current | $V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$ | - | 0.13 | 1 | μA |
| | | $V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ C$ | - | 50 | 100 | μA |
| I_{GSS} | gate leakage current | $V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$ | - | 2 | 100 | nA |
| | | $V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$ | - | 2 | 100 | nA |

N-channel 100 V, 2.9 mOhm MOSFET with enhanced SOA in LPAK88

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|-----------------------------------|---|------|------|-------|------|
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 25 A; T _J = 25 °C; Fig. 12 | - | 2.3 | 2.9 | mΩ |
| | | V _{GS} = 10 V; I _D = 25 A; T _J = 100 °C; Fig. 13 | - | 3.4 | 4.6 | mΩ |
| | | V _{GS} = 10 V; I _D = 25 A; T _J = 175 °C; Fig. 13 | - | 4.8 | 6.7 | mΩ |
| R _G | gate resistance | f = 1 MHz; T _J = 25 °C | 0.4 | 0.83 | 1.65 | Ω |
| Dynamic characteristics | | | | | | |
| Q _{G(tot)} | total gate charge | I _D = 25 A; V _{DS} = 50 V; V _{GS} = 10 V; T _J = 25 °C; Fig. 14 ; Fig. 15 | 63 | 125 | 188 | nC |
| | | I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V; T _J = 25 °C | - | 65 | - | nC |
| Q _{GS} | gate-source charge | I _D = 25 A; V _{DS} = 50 V; V _{GS} = 10 V; T _J = 25 °C; Fig. 14 ; Fig. 15 | 26 | 44 | 61 | nC |
| Q _{GS(th)} | pre-threshold gate-source charge | | - | 26.4 | - | nC |
| Q _{GS(th-pl)} | post-threshold gate-source charge | | - | 17.4 | - | nC |
| Q _{GD} | gate-drain charge | | 6.4 | 21.3 | 49 | nC |
| V _{GS(pl)} | gate-source plateau voltage | I _D = 25 A; V _{DS} = 50 V; T _J = 25 °C; Fig. 14 ; Fig. 15 | - | 4.9 | - | V |
| C _{iss} | input capacitance | V _{DS} = 50 V; V _{GS} = 0 V; f = 1 MHz; T _J = 25 °C; Fig. 16 | 5691 | 9486 | 13280 | pF |
| C _{oss} | output capacitance | | 1317 | 2195 | 3512 | pF |
| C _{rss} | reverse transfer capacitance | | 5 | 47 | 121 | pF |
| t _{d(on)} | turn-on delay time | V _{DS} = 50 V; R _L = 2 Ω; V _{GS} = 10 V; R _{G(ext)} = 5 Ω; T _J = 25 °C | - | 31 | - | ns |
| t _r | rise time | | - | 35 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 61 | - | ns |
| t _f | fall time | | - | 43 | - | ns |
| Source-drain diode | | | | | | |
| V _{SD} | source-drain voltage | I _S = 25 A; V _{GS} = 0 V; T _J = 25 °C; Fig. 17 | - | 0.79 | 1 | V |
| t _{rr} | reverse recovery time | I _S = 25 A; di _S /dt = -100 A/μs; V _{GS} = 0 V; | - | 52 | - | ns |
| Q _r | recovered charge | V _{DS} = 50 V; T _J = 25 °C; Fig. 18 | - | 57 | - | nC |

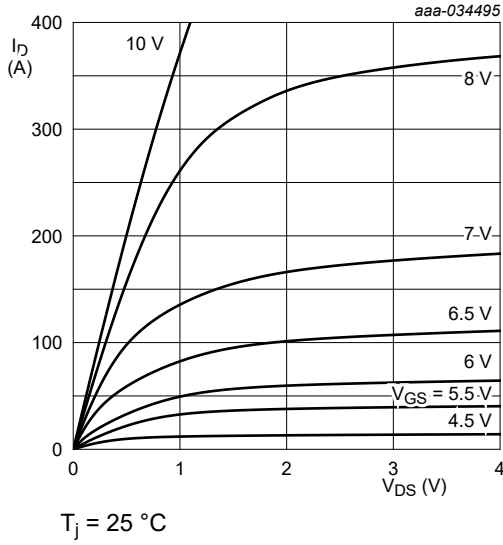


Fig. 8. Output characteristics; drain current as a function of drain-source voltage; typical values

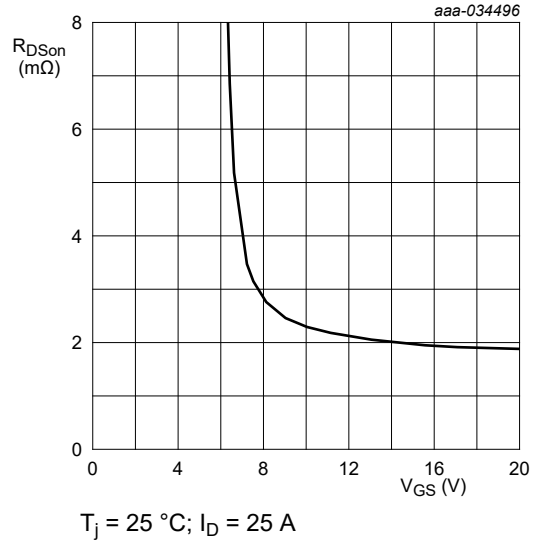


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

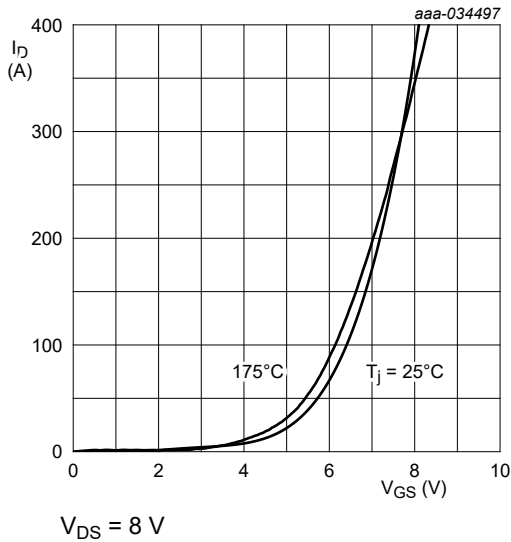


Fig. 10. Transfer characteristics; drain current as a function of gate-source voltage; typical values

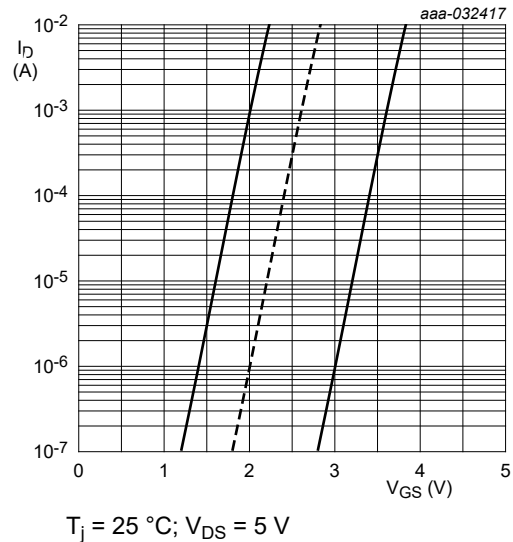


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

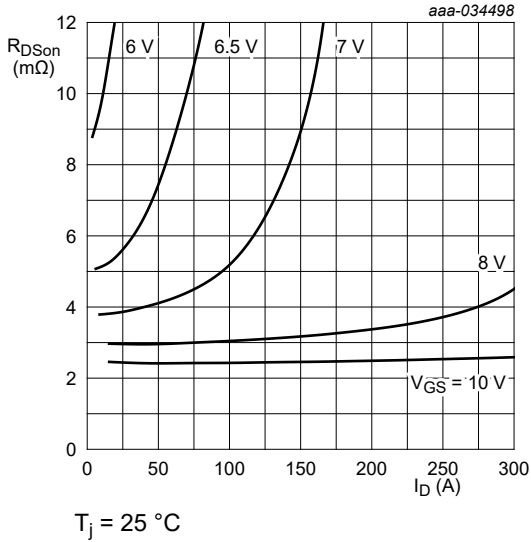
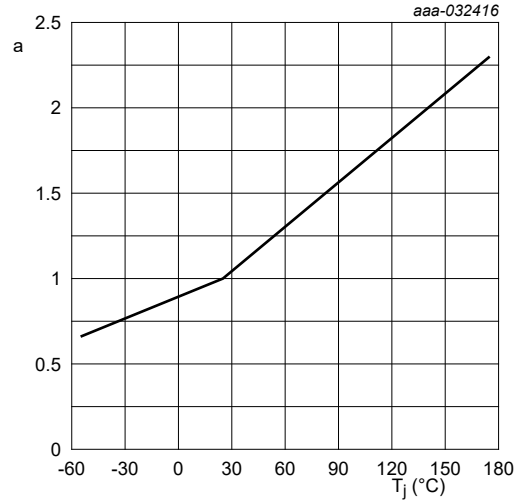


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DS(on)}}{R_{DS(on), (25^\circ\text{C})}}$$

Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

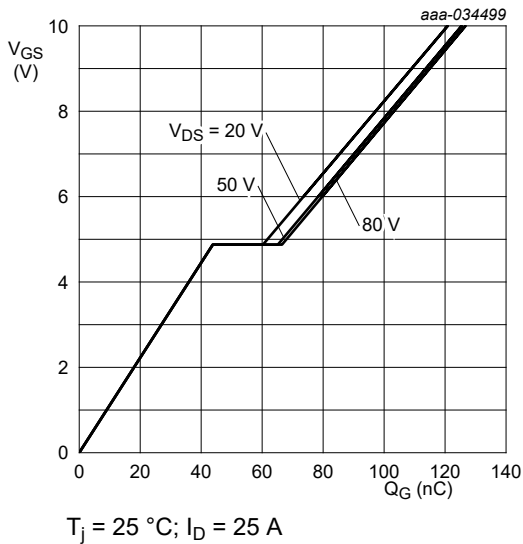


Fig. 14. Gate-source voltage as a function of gate charge; typical values

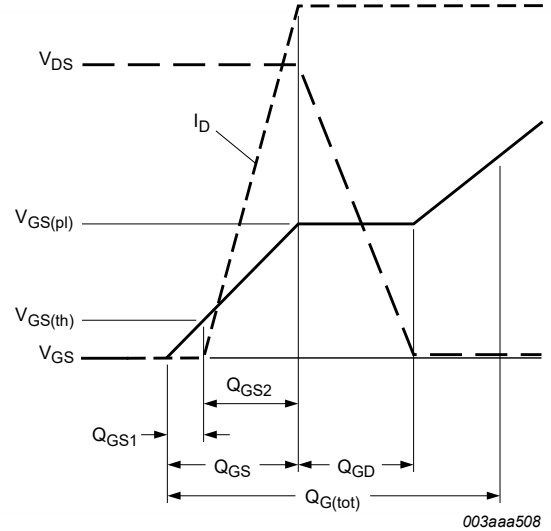
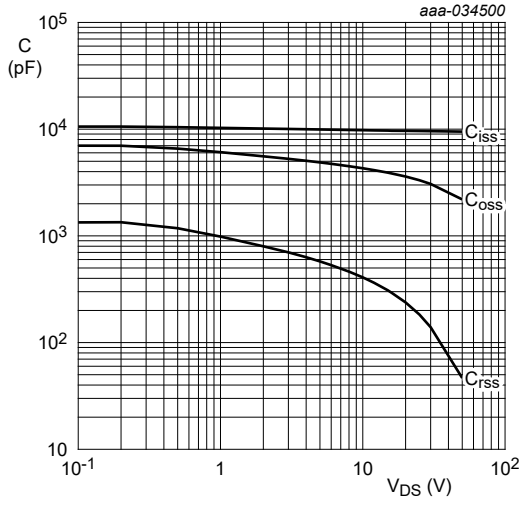
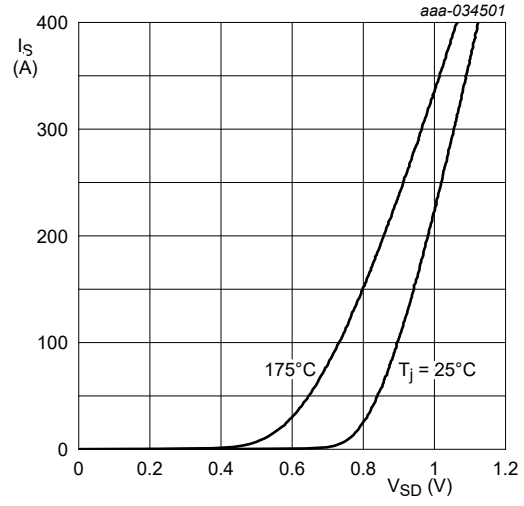


Fig. 15. Gate charge waveform definitions



$V_{GS} = 0$ V; $f = 1$ MHz

Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0$ V

Fig. 17. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

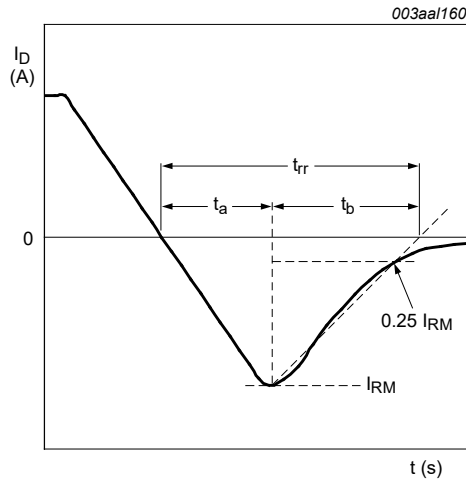


Fig. 18. Reverse recovery timing definition

11. Package outline

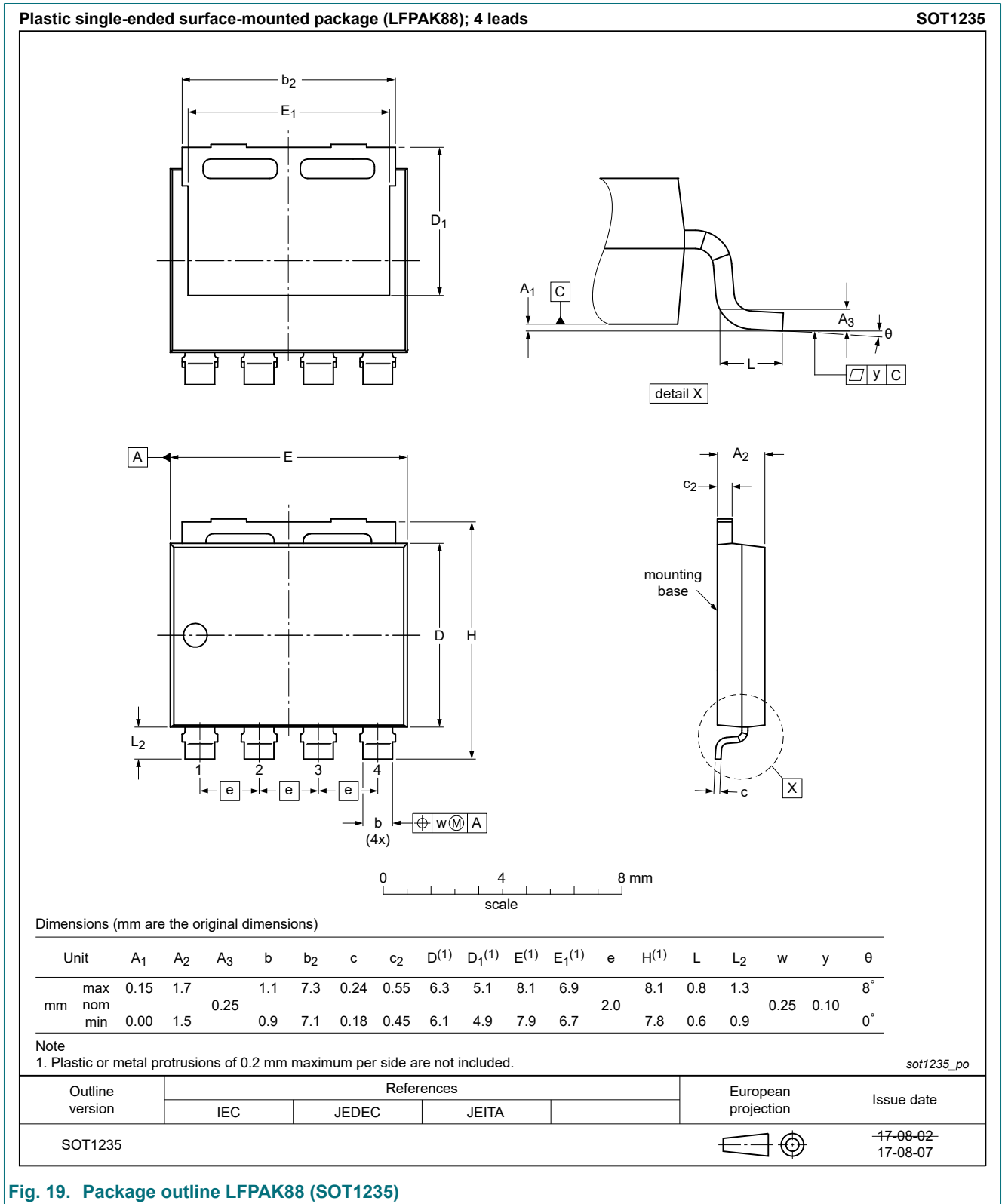


Fig. 19. Package outline LPAK88 (SOT1235)

12. Soldering

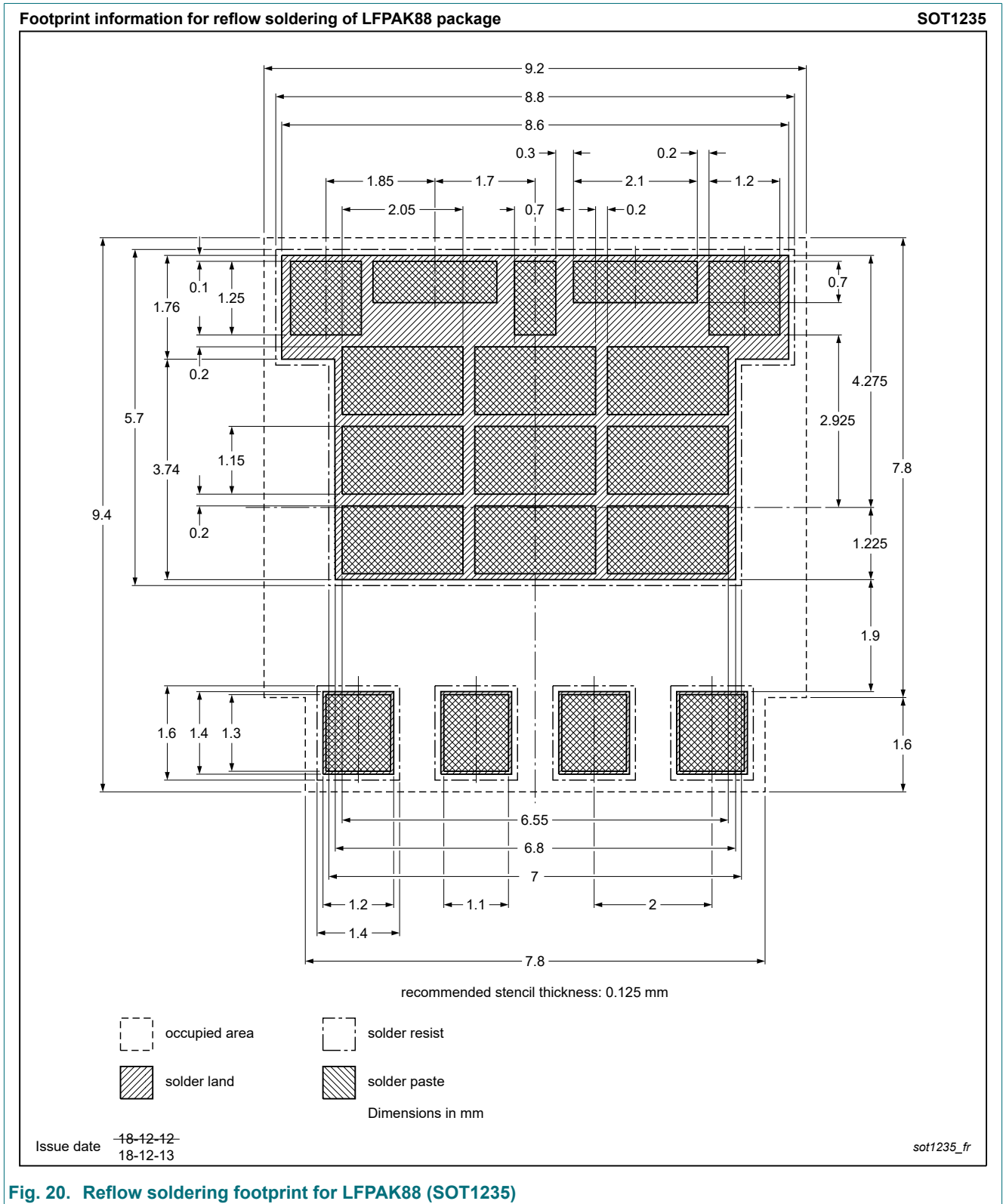


Fig. 20. Reflow soldering footprint for LPAK88 (SOT1235)

13. Legal information

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

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